

# Shigehisa Shibayama

## List of Publications by Year in descending order

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2258059

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#	ARTICLE	IF	CITATIONS
1	Impact of Wet Annealing on Ferroelectric Phase Formation and Phase Transition of HfO <sub>2</sub> –ZrO <sub>2</sub> System. ACS Applied Electronic Materials, 2021, 3, 2203-2211.	4.3	6
2	Lowering of the Schottky barrier height of metal/n-type 4H-SiC contacts using low-work-function metals with thin insulator insertion. Japanese Journal of Applied Physics, 2021, 60, 075503.	1.5	4
3	Impact of oxide/4H-SiC interface state density on field-effect mobility of counter-doped n-channel 4H-SiC MOSFETs. Japanese Journal of Applied Physics, 2022, 61, 021007.	1.5	3
4	Low-temperature formation of Mg/n-type 4H-SiC ohmic contacts with atomically flat interface by lowering of Schottky barrier height. Applied Physics Express, 2022, 15, 015501.	2.4	3
5	Photoluminescence properties of heavily Sb doped Ge <sub>1-x</sub> Sn <sub>x</sub> and heterostructure design favorable for n <sup>+</sup> -Ge <sub>1-x</sub> Sn <sub>x</sub> active layer. Japanese Journal of Applied Physics, 2022, 61, SA1004.	1.5	1
6	Visualization of local strain in 4H-SiC trench metal-oxide-semiconductor field-effect transistor using synchrotron nanobeam X-ray diffraction. Japanese Journal of Applied Physics, 0, , .	1.5	0